Am100415

1024 x 1 IMOX™ II ECL Bipolar RAM

DISTINCTIVE CHARACTERISTICS

- Fast access time (8 ns typ.) improves system cycle
- Enhanced output voltage level compensation providing 6X (improvement in) VOL and VOH stability over supply and temperature ranges
- Internally voltage and temperature compensated providing flat AC performance
- Outputs preconditioned during write cycle eliminating write recovery glitch
- Emitter follower outputs -- easy wire-ORing
 - Power dissipation decreases with increasing temperatura

GENERAL DESCRIPTION

The Am100415 is a fully decoded 1024-bit ECL RAM organized 1024 words by one bit. Bit selection is achieved by means of a 10-bit address, Ao through Ag. Easy memory expansion is provided by an active-LOW chip select (CS) input and an unterminated OR-tieable emitter follower output.

An active-LOW write line (WE) controls the write/read operation of the memory. When the chip select and write lines are LOW, the data input (DIN) is written into the addressed memory word simultaneously preconditioning

the output so true data is present when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the "write recovery alitch."

Reading is performed with the chip select line LOW and the write line HIGH. The information stored in the addressed word is read out on the noninverting output (DOUT).

During the writing operation or when the chip select line is HIGH, the output of the memory goes to a LOW state.



MODE SELECT TABLE

L

L

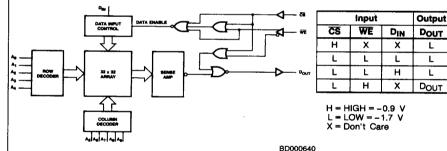
Mode

Not Selected

Write "0"

Write "1"

Read



PRODUCT SELECTOR GUIDE

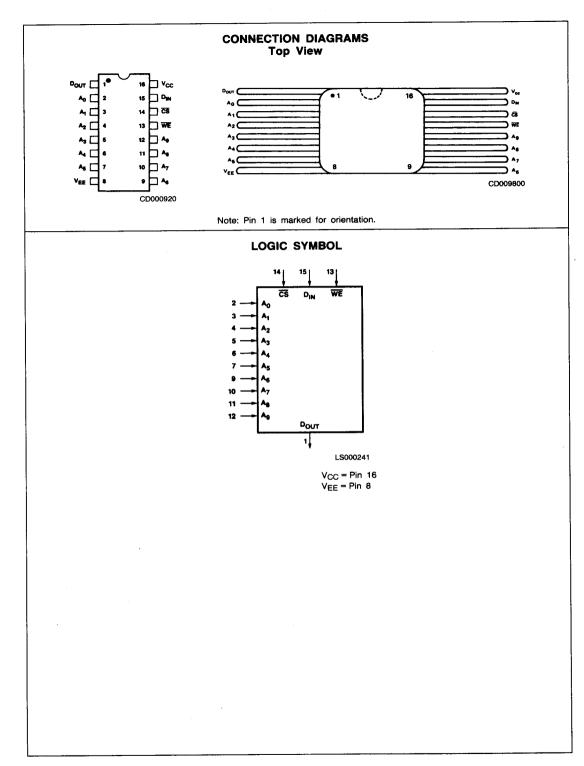
Highlights of Key Performance Parameters (Commercial)

Part Number	Am100415-10	Am100415A	Am100415
Address Access Time (tAA)	10 ns	15 ns	20 ns
Write Pulse Width (tw)	10 ns	10 ns	12 ns
Write Recovery (twR)	10 ns	12 ns	15 ns
Chip Select Access/ Recovery (t _{ACS} /t _{RCS})	8 ns	8 ns	8 ns
Write Disable (tws)	10 ns	10 ns	10 ns
Power Supply (I _{EE})	150 mA	150 mA	150 mA

IMOX is a trademark of Advanced Micro Devices, Inc.

Publication # Amendment Issue Date: May 1986

3-1



ORDERING INFORMATION

Standard Products

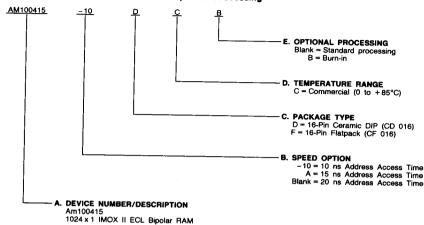
AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: A. Device Number

B. Speed Option (if applicable)

C. Package Type

D. Temperature Range

E. Optional Processing



Valid Combinations						
AM100415-10						
AM100415A	DC, DCB FC, FCB					
Am100415	FC, FCB					

Valid Combinations

B = Burn-in

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature65 to +150°C
Case Temperature with
Power Applied55 to +125°C
VFF Pin Potential to
GND Pin7.0 V to +0.5 V
Input Voltage (DC)VEE to +0.5 V
Output Current (DC Output HIGH)30 mA to +0.1 mA

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices		
Temperature0	to	+85°C
Supply Voltage5.7 V	to	-4.2 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS V_{EE} = -4.5 V, V_{CC} = GND (Note 2)

Parameter Symbol	Parameter Description	Test Co	B(Note 3)	Typ. (Note 1)	A (Note 3)	Units	
VoH	Output Voltage HIGH	VIN = VIHA OF VILB		- 1025	-955	-880	mV
Vol	Output Voltage LOW	- VIN VIAX S. VILE	Loading is	-1810	-1715	- 1620	mV
VOHC	Output Voltage HIGH	VIN = VIHB OF VILA	50 Ω to -2.0 V	- 1035			mV
Volc	Output Voltage LOW	T VIN TIME OF TICK				-1610	mV
ViH	Input Voltage HIGH	Guaranteed Input Voltage 4)	-1165		-880	m∨	
V _{IL}	Input Voltage LOW	Guaranteed Input Voltage 4)	-1810		-1475	mV	
l _{IH}	Input Current HIGH	V _{IN} = V _{IHA}			220	μΑ	
hL	Input Current LOW Chip Select (CS) All Other Inputs	V _{IN} = V _{ILB}		0.5 -50		170	μΑ
IEE	Power Supply Current (Pin 8)	All Inputs and Outputs O	All Inputs and Outputs Open				mA

Notes: 1. Typical values are at VEE = -4.5 V, T = 25°C and maximum loading.

2. Output load = 50 Ω and 30 pF to -2.0 V

T = T_A = 0 to +85°C for Ceramic DIPs.

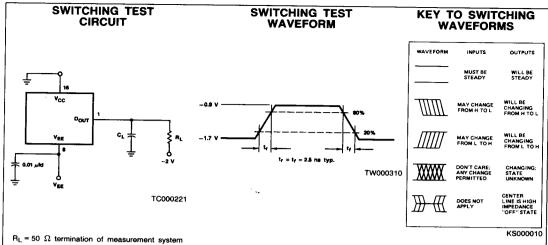
Guaranteed with transverse air flow exceeding 400 linear F.P.M. and 2-minute warm-up period. Approximate resistance values of the package are:

 $\theta_{\rm JA}$ (Junction to Ambient) = 90°C/Watt (still air)

 $\theta_{\rm JA}$ (Junction to Ambient) = 50°C/Watt (at 400 F.P.M. air flow) T = T_C = 0 to +85°C for Flatpacks and Leadless Chip Carriers

 $\theta_{\rm JC}$ (Junction to Case) = 25°C/Watt
3. Definition of symbols and terms used in this product specification: The relative values of the specified conditions and limits will be referenced to an algebraic scale. The extremities of the scale are: "A" the value closest to positive infinity, "B" the value closest to negative infinity.

4. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.



C_L = 30 pF (including stray jig capacitance)

SWITCHING CHARACTERISTICS $V_{EE} = -4.27$ to -4.73 V (Note 2)

No.	Parameter Symbol	Parameter Description	Test Conditions	Am100415A-10			Am100415A			Am 100415			
				Min.	Typ. (Note 1)	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
REAL	MODE										(110.0 1)	I WILLIAM	Oille
1	tacs	Chip Select Access Time	Measured at 50% of input to valid		5	8		5	8		5	8	
2	trics	Chip Select Recovery Time	output (VILA for VOL or VIHB for VOH)		5	8		5	8		5	8	ns
3	tAA	Address Access Time			8	10	-	10	15	-	12	20	
WRIT	E MODE												
4	tw	Write Pulse Width (to Guarantee Writing)	twsa = twsa(Min.)	10	6		10	6		12	9		ns
5	twsp	Data Setup Time Prior to Write		1	0		2	0		4	0		ns
6	twho	Data Hold Time After Write		1	0		2	0		4	0		ns
7	twsa	Address Setup Time Prior to Write	tw = tw(Min.)	1	0		3	3		5	3		ns
8	twha	Address Hold Time After Write		1	0		2	0		3	0		ns
ľ			Measured at 50%	1	0		2	ō		4	0	-	ns
9 twscs	Chip Select Setup of in	of input to valid output (VILA for	1	0		2	0		4	0		ns	
ĺ	• wscs	Prior to Write	VOL or VIHB for		5	10		5	10		5	10	ns
			VOH)		6	10		6	12		7	15	ns
RISE	TIME AND F	ALL TIME		_									
	tr	Output Rise Time	Measured between 20% and 80% points		2.5			2.5			2.5		
	t _f	Output Fall Time			2.5			2.5			2.5		ns
CAPA	CITANCE		·										
- 1	CIN	Input Pin Capacitance	Management with a	T	4	5		4	5	$\overline{}$	4	5	рF
	COUT	Output Pin Capacitance	Measure with a Pulse Technique		7	8		7	8		7	8	pF

